

# PSMN3R3-80BS

# N-channel 80 V, 3.5 m $\Omega$ standard level MOSFET in D2PAK Rev. 2 — 29 February 2012 Product data s

**Product data sheet** 

#### 1. **Product profile**

### 1.1 General description

Standard level N-channel MOSFET in D2PAK package qualified to 175C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

### 1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive

### 1.3 Applications

- DC-to-DC converters
- Load switch

- Motor control
- Server power supplies

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	-	80	V
I <sub>D</sub>	drain current	$T_{mb}$ = 25 °C; $V_{GS}$ = 10 V; see <u>Figure 1</u>	[1] -	-	120	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	-	306	W
Tj	junction temperature		-55	-	175	°C
Static characte	eristics					
R <sub>DSon</sub>	drain-source on-state	$V_{GS} = 10 \text{ V; } I_D = 25 \text{ A; } T_j = 25 \text{ °C; see } \frac{\text{Figure } 13}{\text{ or } 13}$	-	3	3.5	mΩ
		$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 100 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	4.95	5.8	mΩ
Dynamic char	acteristics					
$Q_{GD}$	gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 75 \text{ A}; V_{DS} = 40 \text{ V}; \text{ see } \frac{\text{Figure 14}}{\text{Figure 14}};$	-	28	-	nC
Q <sub>G(tot)</sub>	total gate charge	see <u>Figure 15</u>	-	111	-	nC
Avalanche ruggedness						
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 120 A; $V_{sup} \le$ 80 V; $R_{GS}$ = 50 $\Omega$ ; unclamped	-	-	676	mJ

<sup>[1]</sup> Continuous current is limited by package.



# 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain	mb	D
3	S	source		G (EX)
mb	D	drain	ii	
				mbb076 S
			∐ ∐ 1 3	
			SOT404 (D2PAK)	

# 3. Ordering information

Table 3. Ordering information

Type number			
	Name	Description	Version
PSMN3R3-80BS	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

# 4. Limiting values

Table 4. Limiting values

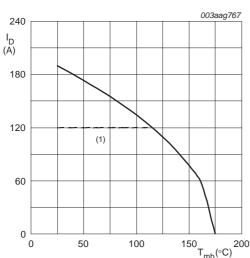
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	80	V
$V_{DGR}$	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$	-	80	V
$V_{GS}$	gate-source voltage		-20	20	V
$I_D$	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 100 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{Model}}$	<u>[1]</u> _	120	Α
		$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{Model}}$	<u>[1]</u> _	120	Α
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25 \text{ °C}$ ; see Figure 3	-	760	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	306	W
T <sub>stg</sub>	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature		-	260	°C
Source-drain	diode				
Is	source current	T <sub>mb</sub> = 25 °C	<u>[1]</u> -	120	Α
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$	-	760	Α
Avalanche ru	iggedness				
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 120 A; $V_{sup}$ ≤ 80 V; $R_{GS}$ = 50 $\Omega$ ; unclamped	-	676	mJ

<sup>[1]</sup> Continuous current is limited by package.

PSMN3R3-80BS

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 $V_{GS} \ge 10 \text{ V}$ ; (1) Capped at 120 A due to package

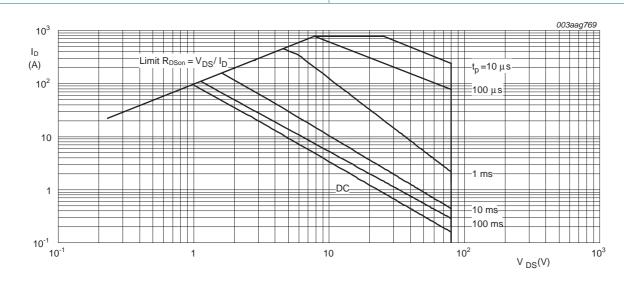
40 0 150 T<sub>mb</sub> (°C) 150 T<sub>mb</sub>(°C)  $P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$ 

120

80

Continuous drain current as a function of Fig 1. mounting base temperature

Normalized total power dissipation as a function of mounting base temperature



 $T_{mb} = 25$  °C;  $I_{DM}$  is a single pulse

Safe operating area; continuous and peak drain currents as a function of drain-source voltage

### 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	0.22	0.49	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	minimum footprint; mounted on a printed circuit board	-	50	-	K/W

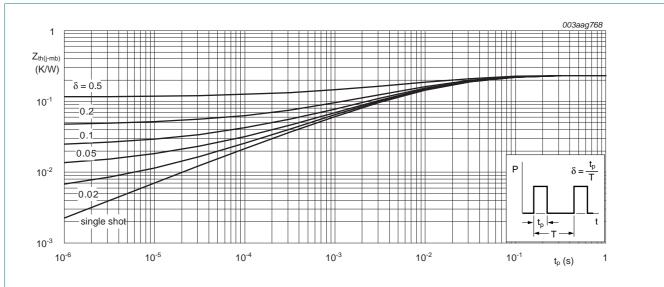


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

# 6. Characteristics

Table 6 Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V <sub>(BR)DSS</sub>	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	73	-	-	V
	breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	80	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}$ ; $V_{DS} = V_{GS}$ ; $T_j = 175 \text{ °C}$ ; see Figure 10	1	-	-	V
		$I_D = 1 \text{ mA}$ ; $V_{DS} = V_{GS}$ ; $T_j = -55 \text{ °C}$ ; see Figure 10	-	-	4.6	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = 25$ °C; see Figure 10;see Figure 11	2	3	4	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 80 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	10	μΑ
		$V_{DS} = 80 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 ^{\circ}\text{C}$	-	-	500	μΑ
$I_{GSS}$	gate leakage current	$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nA
		$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nA
R <sub>DSon</sub> drain-source on-state resistance		$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 175 °C; see <u>Figure 12</u> ;see <u>Figure 13</u>	-	7.1	8.4	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$ see Figure 13	-	3	3.5	mΩ
	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 100 \text{ °C};$ see Figure 12;see Figure 13	-	4.95	5.8	mΩ	
$R_{G}$	internal gate resistance (AC)	f = 1 MHz	-	0.9	-	Ω
Dynamic	characteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	104	-	nC
		$I_D = 75 \text{ A}; V_{DS} = 40 \text{ V}; V_{GS} = 10 \text{ V};$	-	111	-	nC
$Q_{GS}$	gate-source charge	see Figure 14; see Figure 15	-	38	-	nC
$Q_{GS(th)}$	pre-threshold gate-source charge		-	24	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate-source charge		-	14	-	nC
$Q_{GD}$	gate-drain charge		-	28	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	I <sub>D</sub> = 75 A; V <sub>DS</sub> = 40 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	6.1	-	V
C <sub>iss</sub>	input capacitance	$V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	8161	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; see <u>Figure 16</u>	-	701	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	337	-	pF
d(on)	turn-on delay time	$V_{DS} = 40 \text{ V}; R_L = 0.53 \Omega; V_{GS} = 10 \text{ V};$	-	38	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 4.7 \Omega; I_D = 75 A$	-	29	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	94	-	ns
t <sub>f</sub>	fall time		-	33	-	ns

Table 6. Characteristics ... continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Source-dra	in diode					
$V_{SD}$	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C};$ see <u>Figure 17</u>	-	0.8	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = 25 \text{ A}$ ; $dI_S/dt = 100 \text{ A/}\mu\text{s}$ ; $V_{GS} = 0 \text{ V}$ ;	-	59	-	ns
Q <sub>r</sub>	recovered charge	$V_{DS} = 20 \text{ V}$	-	109	-	nC

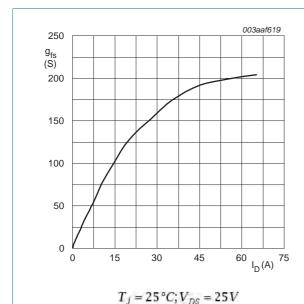


Fig 5. Forward transconductance as a function of drain current; typical values

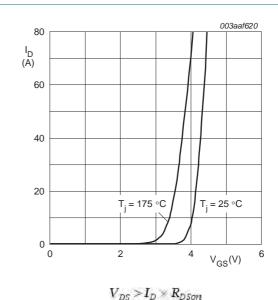


Fig 6. Transfer characteristics: drain current as a

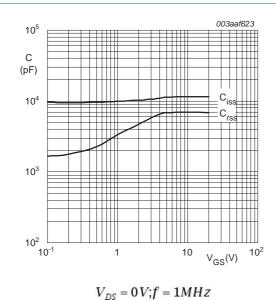


Fig 7. Input and reverse transfer capacitances as a function of gate-source voltage; typical values

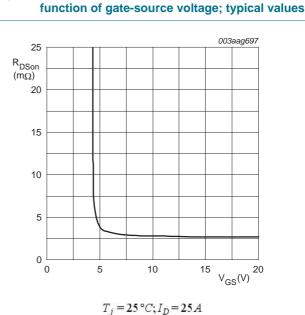
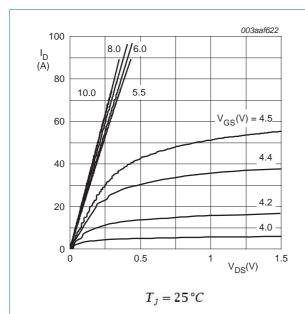


Fig 8. Drain-source on-state resistance as a function of gate-source voltage; typical values



Output characteristics: drain current as a Fig 9. function of drain-source voltage; typical values

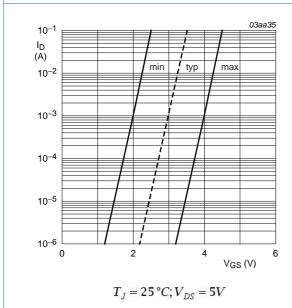
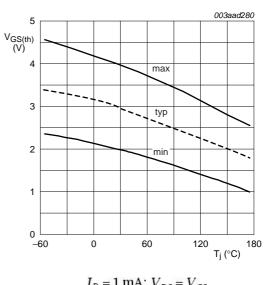


Fig 11. Sub-threshold drain current as a function of gate-source voltage



 $I_D = 1 \text{ mA}; V_{DS} = V_{GS}$ 

Fig 10. Gate-source threshold voltage as a function of junction temperature

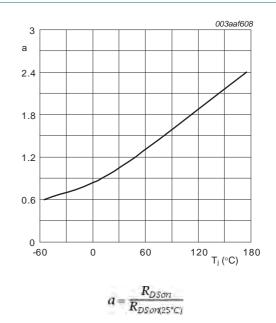


Fig 12. Normailzed drain-source on-state resistance factor as a function of junction temperature

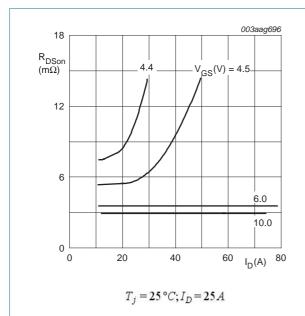


Fig 13. Drain-source on-state resistance as a function of drain current; typical values

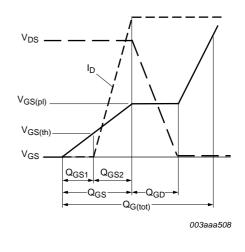


Fig 14. Gate charge waveform definitions

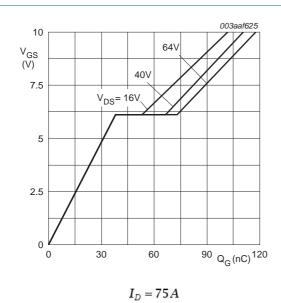
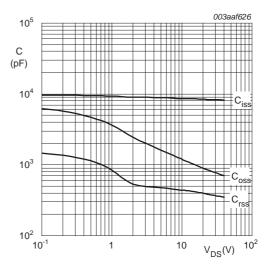


Fig 15. Gate-source voltage as a function of gate charge; typical values



 $V_{GS} = 0V; f = 1MHz$ 

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

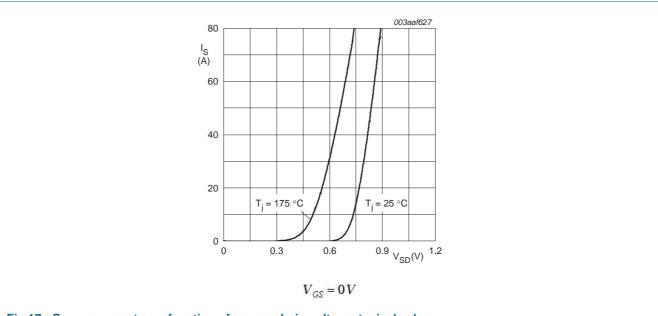


Fig 17. Source current as a function of source-drain voltage; typical values

### 7. Package outline

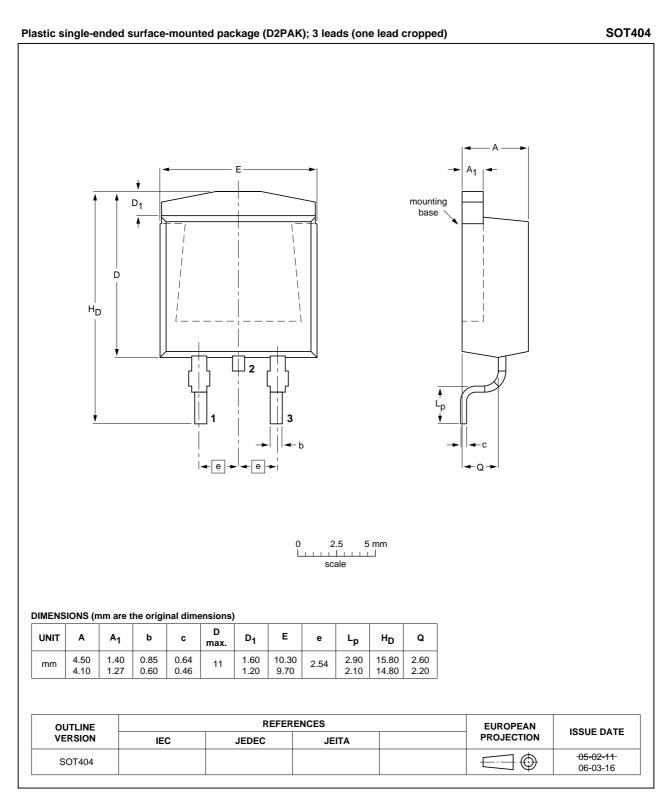


Fig 18. Package outline SOT404 (D2PAK)

# 8. Revision history

### Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN3R3-80BS v.2	20120229	Product data sheet	-	PSMN3R3-80BS v.1
Modifications:	<ul><li>Status changed fr</li><li>Various changes</li></ul>	rom objective to product. to content.		
PSMN3R3-80BS v.1	20110928	Objective data sheet	-	-

### 9. Legal information

### 9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions"
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Nexperia PSMN3R3-80BS

#### N-channel 80 V, 3.5 mΩ standard level MOSFET in D2PAK

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# **PSMN3R3-80BS**

### **Nexperia**

N-channel 80 V, 3.5 m $\Omega$  standard level MOSFET in D2PAK

### 11. Contents

1	Product profile
1.1	General description
1.2	Features and benefits
1.3	Applications
1.4	Quick reference data1
2	Pinning information
3	Ordering information
4	Limiting values
5	Thermal characteristics4
6	Characteristics
7	Package outline
8	Revision history11
9	Legal information12
9.1	Data sheet status
9.2	Definitions12
9.3	Disclaimers
9.4	Trademarks13
10	Contact information



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